first layer. A first terminal zone of the second conduction type is configured adjacent the channel zone. A second terminal zone of the first conduction type is formed in the first layer. Compensation zones of the first conduction type are formed in the first layer. A second layer of the second conduction type is configured between the substrate and the compensation zones. --

## In the Claims:

Please cancel claims 1-14 and please add the following new claims:

## -- 15. A semiconductor component, comprising:

a semiconductor body having a substrate of a first conduction type and a first layer of a second conduction type located above said substrate;

a channel zone of said first conduction type formed in said first layer;

a first terminal zone of said second conduction type configured adjacent said channel zone;

a second terminal zone of said first conduction type formed in said first layer;

compensation zones of said first conduction type formed in said first layer; and

- a second layer of said second conduction type configured between said substrate and said compensation zones.
- 16. The semiconductor component according to claim 15, comprising:
- a boundary zone of said first conduction type extending vertically in said first layer towards said semiconductor body.
- 17. The semiconductor component according to claim 16, wherein said boundary zone extends from said channel zone to said substrate.
- 18. The semiconductor component according to claim 16, wherein said boundary zone is laterally spaced away from said channel zone.
- 19. The semiconductor component according to claim 18, wherein:

said semiconductor body has a first surface; and



said boundary zone extends from said first surface of said semiconductor body to said substrate.

- 20. The semiconductor component according to claim 15, wherein said compensation zones have a pillar-shaped design.
- 21. The semiconductor component according to claim 20, wherein at least some of said compensation zones adjoin said channel zone.
- 22. The semiconductor component according to claim 15, wherein said compensation zones have a spherical design.
- 23. The semiconductor component according to claim 15, wherein:

said compensation zones define first compensation zones;

said first layer has second compensation zones of said second conduction type formed therein;

said second compensation zones are adjacent said first compensation zones; and

10007397.022102

said second compensation zones are doped more neavily than said second layer.

- 24. The semiconductor component according to claim 15, wherein said boundary zone is doped more heavily than said substrate.
- 25. The semiconductor component according to claim 15, wherein:

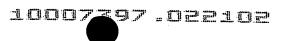
said second terminal zone has a first section extending vertically to said second layer; and

95

said second layer laterally extends at a level;

said second terminal zone has a second section extending laterally at said level of said second layer.

- 26. The semiconductor component according to claim 25, wherein said first section and said second section of said second terminal zone form a well-like structure enclosing said first terminal zone and at least some of said compensation zones.
- 27. The semiconductor component according to claim 15, wherein:



said second terminal zone has a first section extending vertically to said second layer; and

said second terminal zone has a second section extending laterally near said second layer.

- 28. The semiconductor component according to claim 27, wherein said first section and said second section of said second terminal zone form a well-like structure enclosing said first terminal zone and at least some of said compensation zones.
- 29. The semiconductor component according to claim 15, wherein said first layer has a number of dopant atoms of said first conduction type and a number of dopant atoms of said second conduction type that are approximately identical.
- 30. A semiconductor component, comprising:

a semiconductor body having a substrate of a first conduction type and a first layer of a second conduction type located above said substrate;



a second layer of aid second conduction type ormed between said first layer and said substrate, said second layer being doped more weakly than said first layer; and

 $d^{5}$ 

a boundary zone of said first conduction type, said boundary zone vertically extending to said substrate and to said second layer. --